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BTA16-XXXB(MS)

Product specification


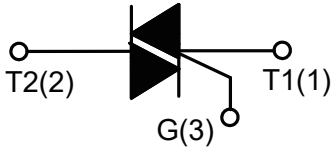


DESCRIPTION

The BTA16-XXXB(MS) series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM} / V_{RRM}	600/800	V

Reference News

PACKAGE OUTLINE	Pin Configuration	Marking	
			
		BTA16-600B(MS)	BTA16-800B(MS)

Notes :XXX represents the order code.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600/800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600/800	V
Non repetitive surge peak Off-state voltage	V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage	V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current($TC=75^\circ\text{C}$)	$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$)	I_{TSM}	160	A
Pt value for fusing ($tp=10\text{ms}$)	Pt	128	A^2s
Critical rate of rise of on-state current ($I_G = 2 \times I_{GT}$)	di/dt	50	$A/\mu s$
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

3 Quadrants

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 33\Omega$	I - II-III	MAX	50	mA
V_{GT}		I - II-III	MAX	1.3	V
V_{GD}	$V_D = V_{DRM}$ $T_j = 125^{\circ}\text{C}$ $R_L = 3.3\text{K}\Omega$	I - II-III	MIN	0.2	V
I_L	$I_G = 1.2I_{GT}$	I-III	MAX	70	mA
		II		80	
I_H	$I_r = 100\text{mA}$		MAX	60	mA
dV/dt	$V_D = 2/3V_{DRM}$ Gate Open $T_j = 125^{\circ}\text{C}$		MIN	1000	V/ μs

4 Quadrants

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 33\Omega$	I - II-III	MAX	50	mA
		IV		70	
V_{GT}		ALL	MAX	1.5	V
V_{GD}	$V_D = V_{DRM}$ $T_j = 125^{\circ}\text{C}$ $R_L = 3.3\text{K}\Omega$	ALL	MIN	0.2	V
I_L	$I_G = 1.2I_{GT}$	I-III-IV	MAX	70	mA
		II		100	
I_H	$I_r = 100\text{mA}$		MAX	60	mA
dV/dt	$V_D = 2/3V_{DRM}$ Gate Open $T_j = 125^{\circ}\text{C}$		MIN	500	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)		Unit
			-600V	-800V	
V_{TM}	$I_{TM} = 22.5\text{A}$ $t_p = 380\mu\text{s}$	$T_j = 25^{\circ}\text{C}$	1.5		V
I_{DRM}	$V_D = V_{DRM}$ $V_R = V_{RRM}$	$T_j = 25^{\circ}\text{C}$	5	5	μA
I_{RRM}		$T_j = 125^{\circ}\text{C}$	1	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case(AC)	2.1	$^{\circ}\text{C}/\text{W}$

FIG.1 Maximum power dissipation versus RMS on-state current

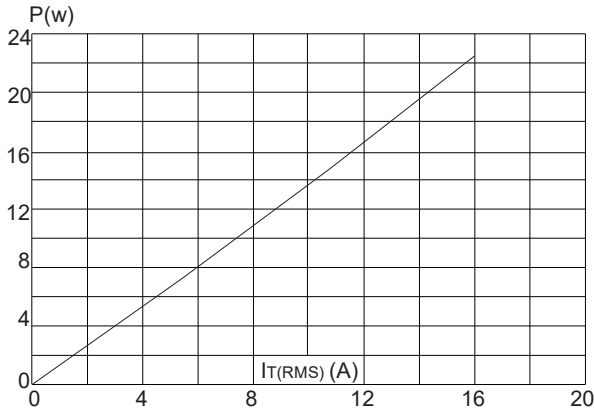


FIG.3: Surge peak on-state current versus number of cycles

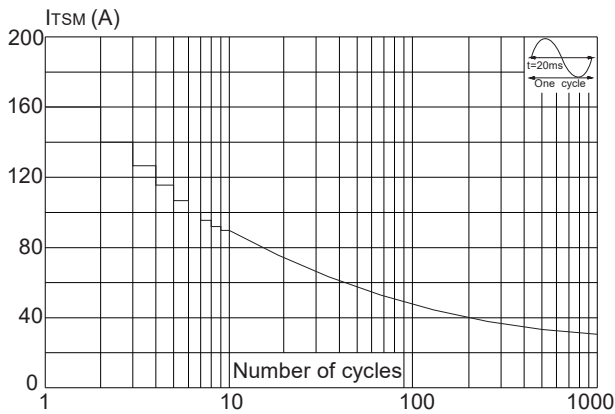


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t ($di/dt < 50A/\mu s$)

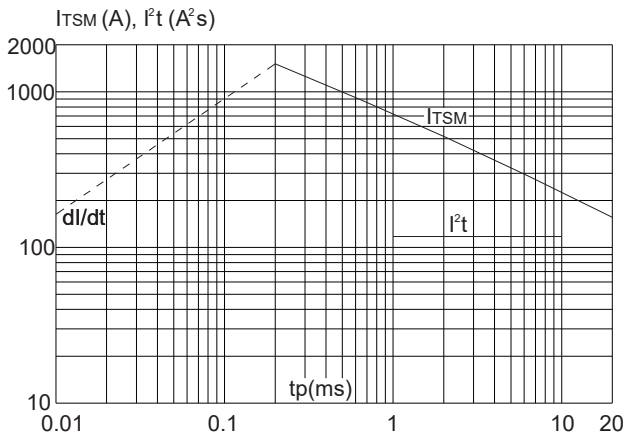


FIG.2: RMS on-state current versus case temperature

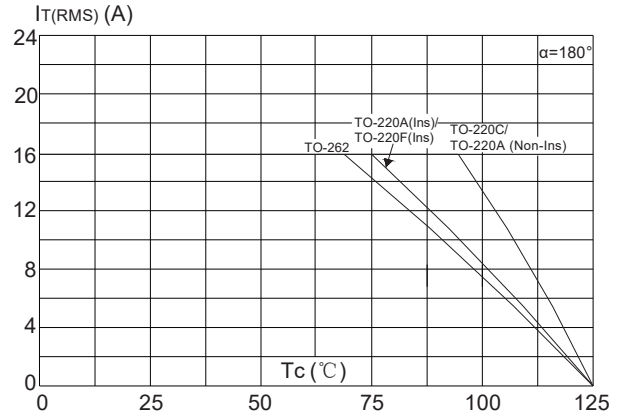


FIG.4: On-state characteristics (maximum values)

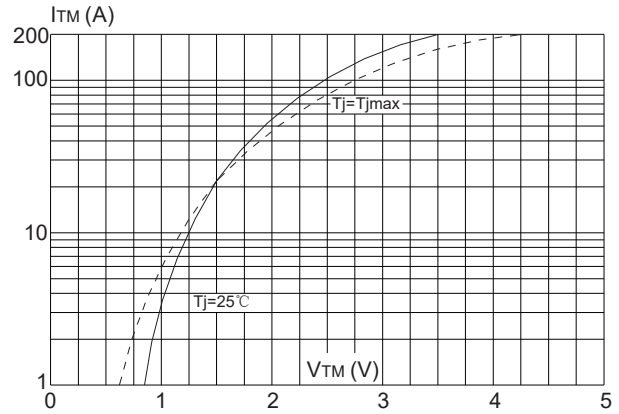
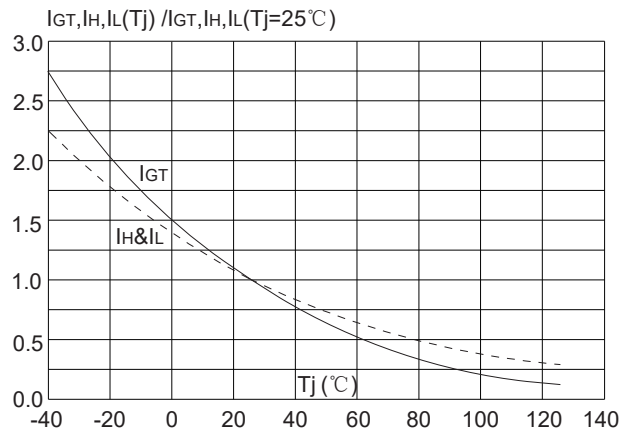
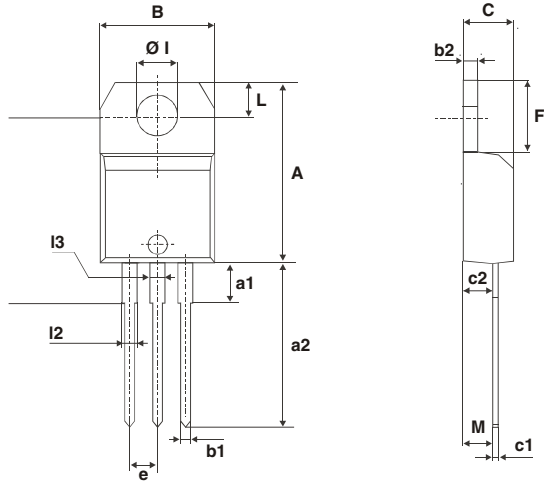


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



PACKAGE MECHANICAL DATA



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
e	2.40		2.70	0.094		0.106
F	6.20		6.60	0.244		0.259
ØI	3.75		3.85	0.147		0.151
I4	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
I2	1.14		1.70	0.044		0.066
I3	1.14		1.70	0.044		0.066
M		2.60			0.102	

REEL SPECIFICATION

P/N	PKG	QTY
BAT16-XXXB(MS)	TO-220	50/One tube 1000/a box of

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